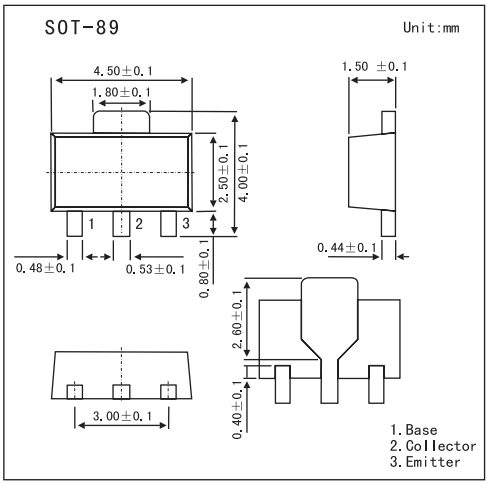
Silicon PNP Epitaxial Planar Type

2SB1589



■ Features

- Low collector to emitter saturation voltage VCE(sat).
- Large collector power dissipation PC.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-10	V
Collector-emitter voltage	V_{CEO}	-10	V
Emitter-base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-2	A
Collector current	I_C	-1.5	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB}= -7 V, I_E = 0			-1	μA
Collector-base voltage	V_{CBO}	I_C = -10 μA, I_E = 0	-10			V
Collector-emitter voltage	V_{CEO}	I_C = -1 mA, I_B = 0	-10			V
Emitter-base voltage	V_{EBO}	I_E = -10 μA, I_C = 0	-7			V
Forward current transfer ratio	h_{FE}	V_{CE} = -1 V, I_C = -400 mA	200		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -1A, I_B = - 25 mA		-0.24	-0.35	V
Transition frequency	f_T	V_{CB} = -6 V, I_E = 50 mA, f = 200 MHz		190		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10V, I_E = 0, f = 1 MHz		6.5		pF
Forward voltage	V_F	I_F = -500 mA			1.3	V

■ Marking

Marking	1U